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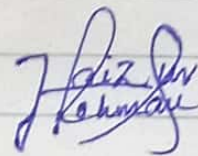
Course title

Electronic Device  
& circuit

Date

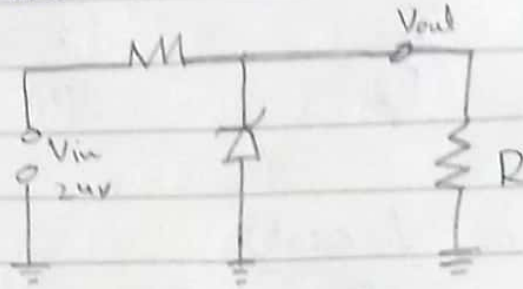
29-9-2020

Student Sign



Q1

From Data Sheet



from the Data sheet 1N4747A

$$V_z = 20 \quad I_z = 12.5 \quad \& \quad Z_z = 22\Omega$$
$$I_{zk} = 0.25$$

(a) for  $I_{zk} \rightarrow$

$$V_{out} = V_z - \Delta I_z Z_z$$

$$= 20 - (I_z - I_{zk}) Z_z$$
$$= 20 - (12.25)(22\Omega)$$
$$= 20 - (0.01225)(22)$$
$$= 20 - 0.2695$$
$$= 19.7305 V$$

Calculating the Zener Max Current dissipation is 1w power

$$I_{zm} = \frac{P_D(\max)}{V_z} = \frac{1w}{20} = 0.05$$

$$I_{zm} = 50mA$$

for  $I_{ZM}$

$$\begin{aligned}V_{out} &= V_Z + \Delta I_Z Z_Z \\&= 20V + (I_{ZM} - I_Z) Z_Z \\&= 20V + (50mA - 12.5mA) 22\Omega \\&= 20V + (37.5mA) 22 \\&= 20V + 0.825\end{aligned}$$

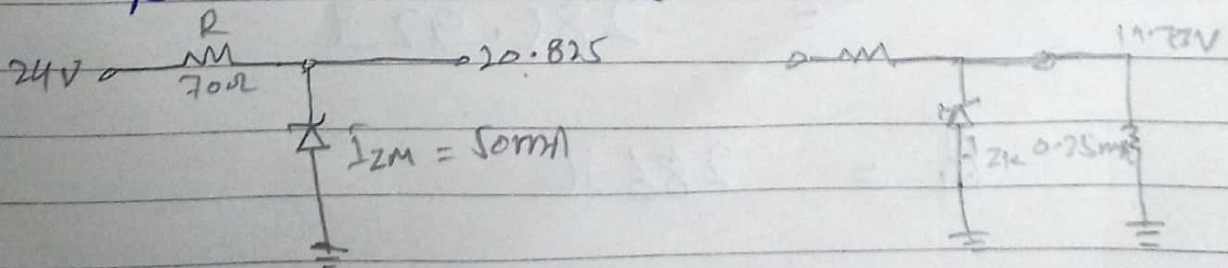
$$V_{out} = 20.825V$$

(b) Calculate the value of  $R$  for maximum Zener Current when there is no load as shown in figure

$$\begin{aligned}R &= \frac{V_{in} - V_{out}}{I_{ZM}} \\&= \frac{24V - 20.825V}{50mA}\end{aligned}$$

$$R = 63.5\Omega$$

$$R = 70\Omega \text{ (Nearest largest standard)}$$



(c) for maximum load Resistance  
(maximum current) The Zener  
diode current minimum ( $I_{zk} = 0.25$ )

$$I_T = V_{in} - V_{out}/R$$

$$= \frac{24V - 19.73V}{70V}$$

$$= 0.061A$$

$$= 0.061A$$

$$I_T = 61mA$$

$$I_L = I_T - I_{zk}$$

$$= 61 - 0.25mA$$

$$I_L = 60.75mA$$

$$R_L = \frac{V_{out}}{I_L} = \frac{19.3}{60.75mA}$$

$$= 19.3 / 0.0675$$

$$= 285.92\Omega$$

$$R_L = 286\Omega$$

Q2

$$V_{BE} = 0.7V$$

$$\Rightarrow I_B = \frac{V_{BB} - V_{BE}}{R_B} = \frac{5V - 0.7V}{3.9k\Omega} = 1102 \mu A$$

$$\Rightarrow I_C = \beta_{DC} I_B \Rightarrow (150)(1102) = 165.3 \text{ mA}$$

$$\Rightarrow I_E = I_C + I_B = 165.3 \text{ mA} + 1102 \mu A$$
$$\Rightarrow 166.4 \text{ mA}$$

Solve for  $V_{CE}$  &  $V_{CB}$

$$V_{CE} = V_{CC} - I_C R_C = 15V - (165.3 \text{ mA})(180\Omega)$$

$$\Rightarrow 15V - 29.7V$$

$$= -14.7V$$

$$V_{CB} = V_{CE} - V_{BE} \Rightarrow -14.7V - 0.7V$$

$$\Rightarrow -15.4V$$

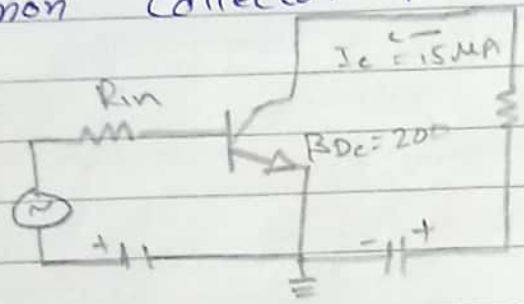
Since the collector is at a lower voltage than the base the collector base junction is forward biased.

Q3

Using BJT as an amplifier we need to set them in Active region because BJT working as an amplifier when we is active region

Transistor has three Basic configuration for using it in Amplification mode

- Common Base : Voltage Gain No current
- Common Emitter : Both Gain
- Common Collector : Current Gain no Voltage.



this is common emitter configuration of transistor which has both voltage and current amplification

$$I_c = \beta I_B$$

$$= 200 + 5\mu A$$

$$I_c = 200 \cdot 0.00005 \mu A$$

$$I_E = I_C + I_B$$

$$I_E = 200.00005 \mu A + 15 \mu A$$

$$I_E = 200.00002$$

Q4

Transistor Fully (ON)

// fully (OFF)

Input & base are at 0V (OFF)

Collector current  $I_c = 0$  (OFF)

$V_{CE} = V_{CC}$  (OFF)

BE Junction is Reverse bias (OFF)

BC Junction is Forward bias (OFF)

Maximum of saturation current  $I_c$  flow (ON)

BE Junction is Forward bias (ON)

BC Junction is forward bias (ON)

$V_{CE} = 0V$  (ON)

BE junction is less than 0.7V (OFF)

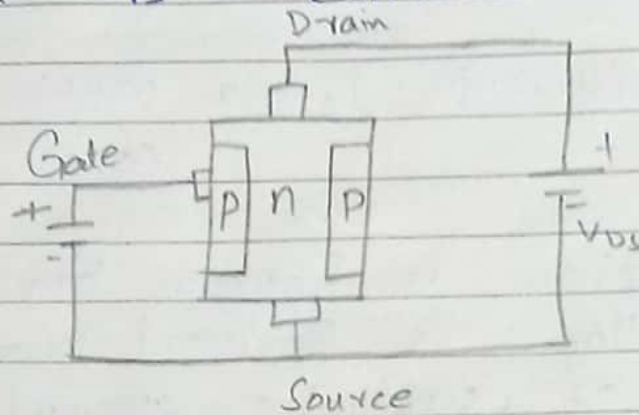
OFF

ON

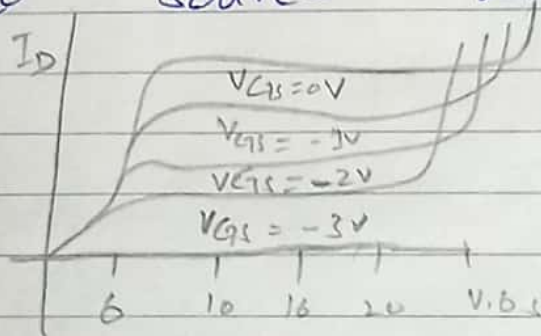


Q5 :-> Junction JFET is type of field effect transistor

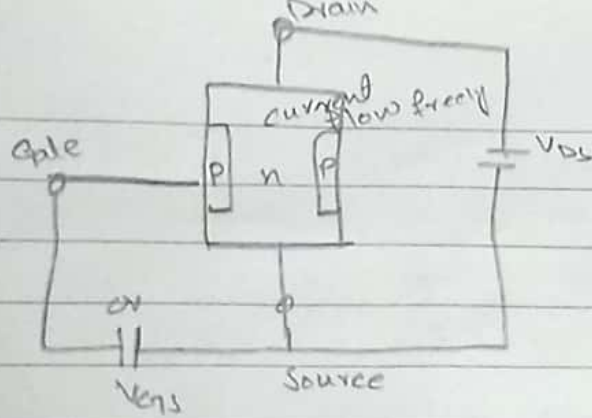
which is voltage controlled device as differ from BJT which is current controlled



Actually FET The drain to source current is controlled by width of channel the E-Field is produced by the gate to source voltage.

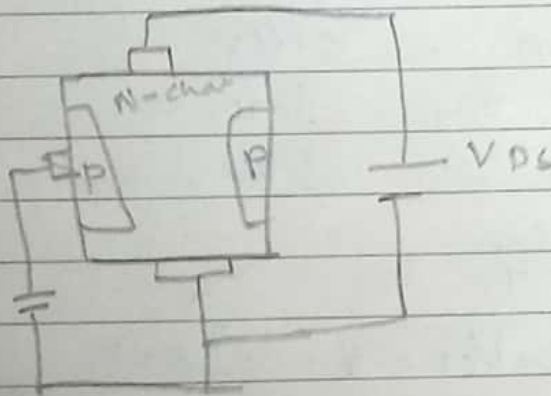


If we see to graph with the no voltage applied to the gate the current flow freely.



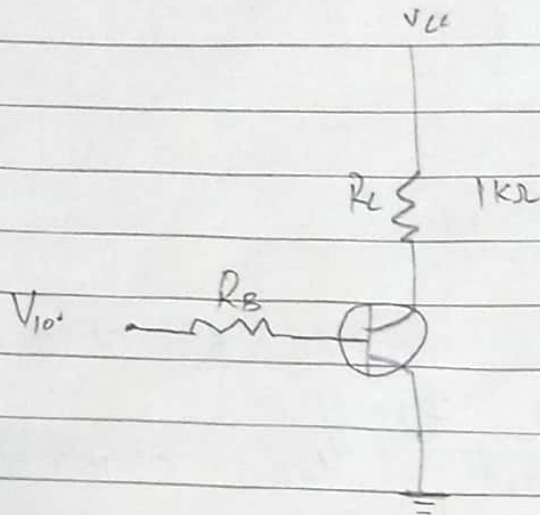
Channel are wider & drain current moves freely.

if we move the channel width start decrease & current cannot move.



So  $V_{gs}$  is more negative  
 so no current flow &  
 this effect is called Pinch  
 off region no current or  
 less current flows.

Q6



Given data  $\rightarrow$

$$\beta_{DC} = 125$$

$$V_{CE(sat)} = 0.4V$$

$$V_{CC} = 10V$$

$$R_C = 1k\Omega$$

Required

$$V_{CE} = ? \quad I_B = ?$$

Sol  $\rightarrow$

(a)  $V_{CE} = ?$

$$V_{in} = 0N$$

When  $V_{in} = 0N$  so transistor  
is in cut off mode and

$$V_{CE} = V_{CC} = 10V$$

(b)  $\min I_B = ?$

$$\beta_{DC} = 125$$

$$V_{CE} = 0.4$$

$$I_c(\text{sat}) = \frac{V_{cc}}{R_c} = \frac{10}{1k\Omega} = 10\text{mA}$$

$$I_{B(\text{min})} = \frac{I_c(\text{sat})}{\beta_{DC}} \\ = \frac{10\text{mA}}{125} = 80\mu\text{A}$$